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Author

Reklaitis A.

Author Unabbreviated

Reklaitis A.

Author/Editor Affiliation

Reklaitis A. : Centre for Physical Sciences and Technology, Semiconductor Physics Institute, A. Gostauto 11, Vilnius LT-01108, Lithuania

Title

Efficient Terahertz Emission from InGaN/GaN Heterostructure

Source

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Abstract

Terahertz emission from the freestanding InGaN/GaN heterostructure illuminated by femtosecond optical pulse is considered using Monte Carlo simulations. The results of Monte Carlo simulations show that the power of terahertz emission from InGaN/GaN heterostructure exceeds the power of the emission from InN surface by one order of magnitude. (10 References).